

ESDAULC6-3BP6 ESDAULC6-3BF2

ESD protection for high speed interface

Main applications

Where transient overvoltage protection in ESD sensitive equipment is required, such as:

- Computers
- Printers
- Communication systems
- Cellular phones handsets and accessories
- Video equipment

Features

- Ultra low capacitance 1.25 pF max.
- Bi-directional protection
- RoHS package

Description

The ESDAULC6-3Bxx is a monolithic application specific discrete device dedicated to ESD protection of high speed interfaces such as USB2.0.

The device is ideal for applications where both reduced print circuit board space and power absorption capability are required.

Benefits

- Ultra low capacitance bidirectional ESD protection
- Low PCB space consumption:
 2.5 mm² max footprint (1.7 mm² for Flip-Chip)
- Enhanced ESD protection:
 - 15 kV contact discharge
 - 15 kV air discharge
- No insertion loss to 3.0 GHz
- Ultra low leakage current
- High reliability offered by monolithic integration

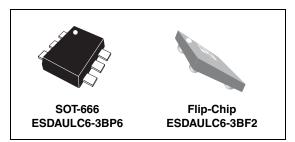


Figure 1. Functional diagram

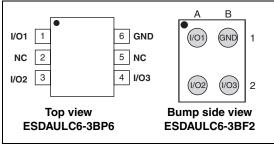


Figure 2. Pin configuration

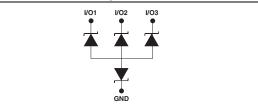


Table 1.Order codes

Part number	Marking
ESDAULC6-3BP6	3
ESDAULC6-3BF2	3B

Complies with the following standards:

IEC 61000-4-2 level 4:

8 kV (contact discharge) 15 kV (air discharge)

MIL STD 883G-Method 3015-7: class 3B

HBM (Human Body Model)

July 2007

1 Characteristics

Table 2.	Absolute maximum ratings
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Symbol	Pa	Value (min.)	Unit	
V _{PP}	V _{PP} Peak pulse voltage ⁽¹⁾ IEC 61000-4-2 contact IEC 61000-4-2 air disch		15 15	kV
Тj	Maximum operating junction tem	150	°C	
T _{stg}	Storage temperature range	-55 to +150	°C	
ΤL	Maximum lead temperature for s	260	°C	

1. For a surge greater than the maximum values, the diode will fail in short-circuit.

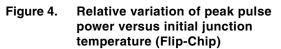
Table 3. Electrical characteristics ($T_{amb} = 25^{\circ} C$)

Symbol	Parameter			+ I			
V _{RM}	Stand-off voltage						
V _{BR}	Breakdown voltage						
V _{CL}	Clamping voltage		.,				
I _{RM}	Leakage current	V _{CL} V _{BR} V _{RM}		I _{RM}	V _{RM} V _E		
I _{PP}	Peak pulse current						
αΤ	Voltage temperature coefficient						
С	Capacitance) Slo	Slope: 1/R _d				
R _d	Dynamic resistance	+		I			
Parameter	Test condition		Min	Тур	Max	Unit	
V _{BR} ⁽¹⁾	I _R = 1 mA		6.0		9.2	V	
I _{RM}	V _{RM} = 5 V				0.5	μA	
R _d	Square pulse, $I_{PP} = 6 \text{ A}$, $t_p = 2.5 \ \mu\text{s}$			1.4		Ω	
αΤ					1.2	10 ⁻⁴ /°C	
	$V_{I/O} = 0 V,$	SOT-666		1.0	1.25		
C	$F = 1 MHz, V_{OSC} = 30 mV$	Flip-Chip		1.25	1.5	ъĘ	
C _{i/o-i/o}	F = 1 MHz, V_{OSC} = 30 mV $V_{I/O}$ = 1.65 V, V_{CC} = 4.3 V, F = 1 MHz, V_{OSC} = 400 mV	Flip-Chip SOT-666		1.25 0.75	1.5 0.9	pF	

1. Same value for I/O to I/O and I/O to GND

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Figure 3. Relative variation of peak pulse power versus initial junction temperature (SOT-666)



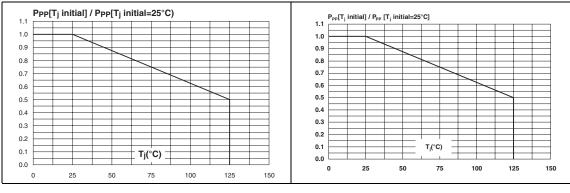
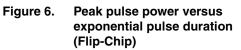
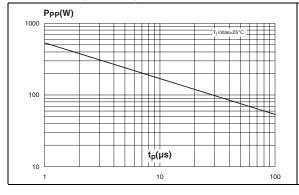


Figure 5. Peak pulse power versus exponential pulse duration (SOT-666)





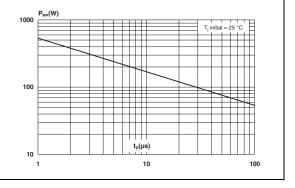
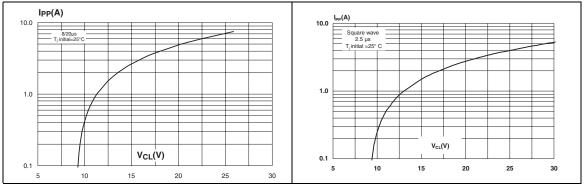


Figure 7. Clamping voltage versus peak pulse current (typical values) (SOT-666)





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Figure 9. Junction capacitance versus reverse voltage applied (typical values) (SOT-666)

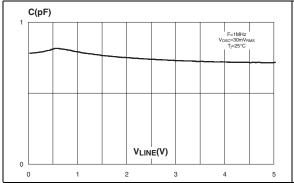
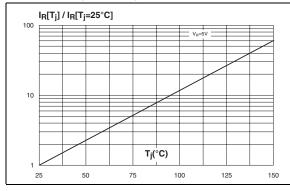
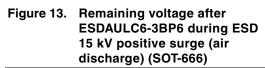
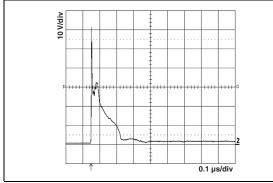
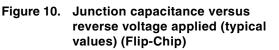


Figure 11. Relative variation of leakage current versus junction temperature (typical values) (SOT-666)









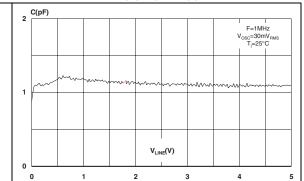


Figure 12. Relative variation of leakage current versus junction temperature (typical values) (Flip-Chip)

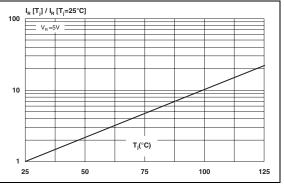
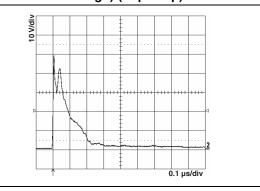
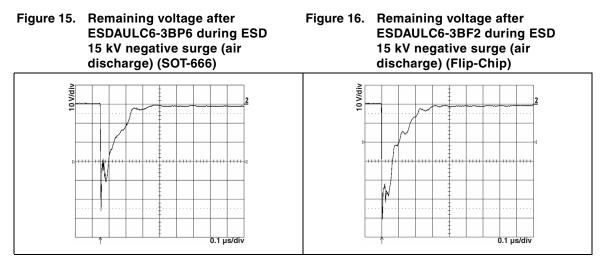
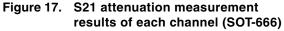
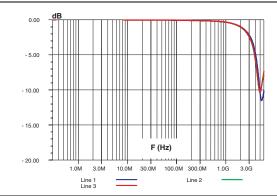


Figure 14. Remaining voltage after ESDAULC6-3BF2 during ESD 15 kV positive surge (air discharge) (Flip-Chip)









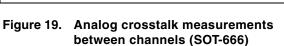


Figure 18. S21 attenuation measurement results of channel 1 (Flip-Chip)

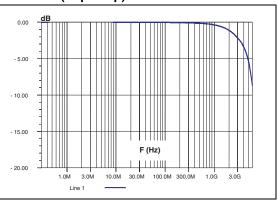
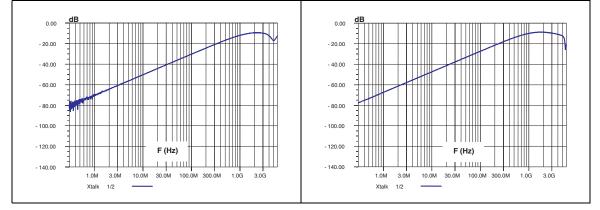


Figure 20. Analog crosstalk measurements between channels (Flip-Chip)



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2 Application examples

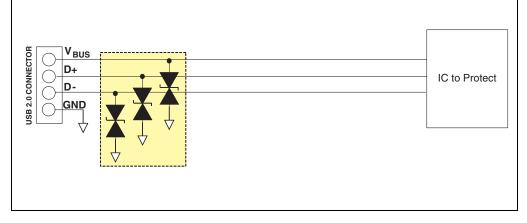


Figure 21. USB2.0 (high speed) protection application schematic

Figure 22. Audio jack protection application schematic

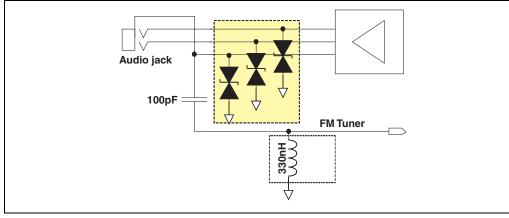
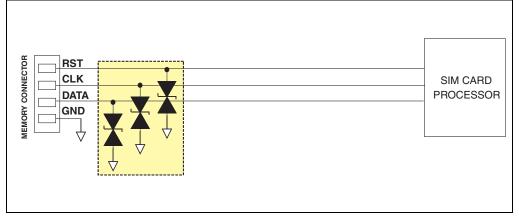


Figure 23. SIM card protection application schematic



3 Ordering information scheme

	ESDA ULC 6-3 B xx
ESD Array	
Ultra low capacitance	
Breakdown Voltage	
6 = 6 Volts	
Number of lines protected	
3 = 3 lines	
Туре	
B = Bidirectional	
Packages	
F2 = Flip-Chip	
P6 = SOT-666	



4 Package information

• Epoxy meets UL 94, V0

Table 4.SOT-666 dimensions

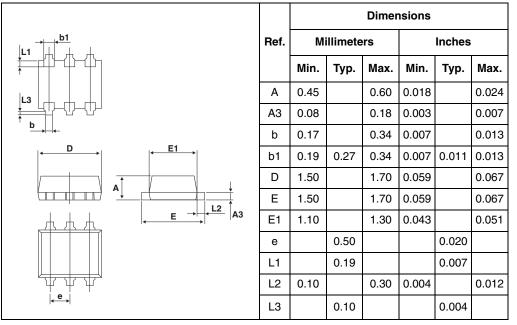


Figure 24. SOT-666 footprint (dimensions in mm)

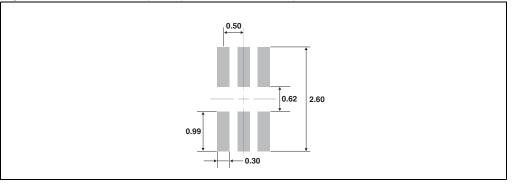


Figure 25. Flip-Chip dimensions

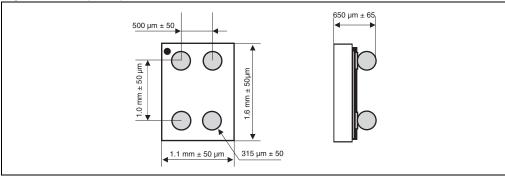




Figure 27. Flip-Chip marking

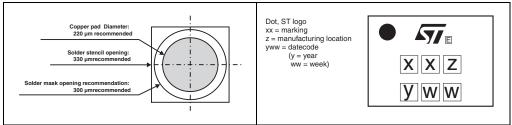
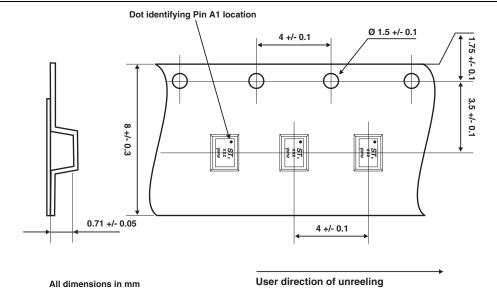


Figure 28. Flip-Chip tape and reel specifications



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



5 Ordering information

Table 5. Ordering information

Part number	Marking	Package	Weight	Base qty	Delivery mode	
ESDAULC6-3BP6	3	SOT-666	2.9 mg	5000	Tape and reel	
ESDAULC6-3BF2	3B	Flip-Chip	2.22 mg	5000	Tape and reel	

6 Revision history

Table 6.Revision history

Datet	Revision	Changes
03-Jul-2007	1	Initial release

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